Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A ferroelectric film including a perovskite ferroelectric or a bismuth layer-structured ferroelectric shown by ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ (wherein A represents at least one ion selected from the group consisting of Li^+, Na^+, K^+, Pb^{2+}, Ca^{2+}, Sr^{2+}, Ba^{2+}, Bi^{3+} and La^{3+}, B represents at least one ion selected from the group consisting of Fe^{3+}, Ti^{4+}, Zr^{4+}, Nb^{5+}, Ta^{5+}, W^{6+} and Mo^{6+}, and m is a natural number),

wherein at least four-fold coordinated Si^{4+} or Ge^{4+} is included in the A site ion.

2. (Original) A ferroelectric film including a perovskite ferroelectric or a bismuth layer-structured ferroelectric shown by ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ (wherein A represents at least one ion selected from the group consisting of Li^+, Na^+, K^+, Pb^{2+}, Ca^{2+}, Sr^{2+}, Ba^{2+}, Bi^{3+} and La^{3+}, B represents at least one ion selected from the group consisting of Fe^{3+}, Ti^{4+}, Zr^{4+}, Nb^{5+}, Ta^{5+}, W^{6+} and Mo^{6+}, and m is a natural number),

wherein at least four-fold coordinated Si^{4+} or Ge^{4+} is included in the A site ion; and

wherein the ferroelectric film is a solid solution with a dielectric shown by X_2SiO_5, $X_4Si_3O_{12}$, X_2GeO_5 or $X_4Ge_3O_{12}$ (wherein X represents Bi^{3+}, Fe^{3+}, Sc^{3+}, Y^{3+}, La^{3+}, Ce^{3+}, Pr^{3+}, Nd^{3+}, Pm^{3+}, Sm^{3+}, Eu^{3+}, Gd^{3+}, Tb^{3+}, Dy^{3+}, Ho^{3+}, Er^{3+}, Tm^{3+}, Yb^{3+} or Lu^{3+}).

3. (Original) A ferroelectric film including a perovskite ferroelectric or a bismuth layer-structured ferroelectric shown by ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ (wherein A represents at least one ion selected from the group consisting of Li^+, Na^+, K^+, Pb^{2+}, Ca^{2+}, Sr^{2+}, Ba^{2+}, Bi^{3+}

and La^{3+}, B represents at least one ion selected from the group consisting of Fe^{3+}, Ti^{4+}, Zr^{4+}, Nb^{5+}, Ta^{5+}, W^{6+} and Mo^{6+}, and m is a natural number),

wherein at least four-fold coordinated Si^{4+} or Ge^{4+} is included in the A site ion; and

wherein the ferroelectric film includes at least one transition element in an amount of 5 to 40 mol% in total, the transition element having the maximum positive valence which is +1 or more greater than the valence of the A site ion of the ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$.

4. (Original) A ferroelectric film including a perovskite ferroelectric or a bismuth layer-structured ferroelectric shown by ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ (wherein A represents at least one ion selected from the group consisting of Li^+, Na^+, K^+, Pb^{2+}, Ca^{2+}, Sr^{2+}, Ba^{2+}, Bi^{3+} and La^{3+}, B represents at least one ion selected from the group consisting of Fe^{3+}, Ti^{4+}, Zr^{4+}, Nb^{5+}, Ta^{5+}, W^{6+} and Mo^{6+}, and m is a natural number),

wherein at least four-fold coordinated Si^{4+} or Ge^{4+} is included in the A site ion; and

wherein the ferroelectric film includes at least one transition element in an amount of 5 to 40 mol% in total, the transition element having the maximum positive valence which is +1 or more greater than the valence of the B site ion of the ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$.

5. (Original) A ferroelectric film including a perovskite ferroelectric or a bismuth layer-structured ferroelectric shown by ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ (wherein A represents at least one ion selected from the group consisting of Li^+, Na^+, K^+, Pb^{2+}, Ca^{2+}, Sr^{2+}, Ba^{2+}, Bi^{3+} and La^{3+}, B represents at least one ion selected from the group consisting of Fe^{3+}, Ti^{4+}, Zr^{4+}, Nb^{5+}, Ta^{5+}, W^{6+} and Mo^{6+}, and m is a natural number),

wherein at least four-fold coordinated Si^{4+} or Ge^{4+} is included in the A site ion;

wherein the ferroelectric film includes at least one transition element having the maximum positive valence which is +1 or more greater than the valence of the B site ion of the ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$;

wherein the ferroelectric film includes at least one transition element having the maximum positive valence which is +1 or more greater than the valence of the A site ion of the ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$; and

wherein the transition elements are included in an amount of 5 to 40 mol% in the A and B sites in total.

6. (Original) A ferroelectric film including a perovskite ferroelectric or a bismuth layer-structured ferroelectric shown by ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ (wherein A represents at least one ion selected from the group consisting of Li^+, Na^+, K^+, Pb^{2+}, Ca^{2+}, Sr^{2+}, Ba^{2+}, Bi^{3+} and La^{3+}, B represents at least one ion selected from the group consisting of Fe^{3+}, Ti^{4+}, Zr^{4+}, Nb^{5+}, Ta^{5+}, W^{6+} and Mo^{6+}, and m is a natural number),

wherein at least four-fold coordinated Si^{4+} or Ge^{4+} is included in the A site ion;

wherein the ferroelectric film is a solid solution with a dielectric shown by X_2SiO_5, $X_4Si_3O_{12}$, X_2GeO_5 or $X_4Ge_3O_{12}$ (wherein X represents Bi^{3+}, Fe^{3+}, Sc^{3+}, Y^{3+}, La^{3+}, Ce^{3+}, Pr^{3+}, Nd^{3+}, Pm^{3+}, Sm^{3+}, Eu^{3+}, Gd^{3+}, Tb^{3+}, Dy^{3+}, Ho^{3+}, Er^{3+}, Tm^{3+}, Yb^{3+} or Lu^{3+}); and

wherein the ferroelectric film includes at least one transition element in an amount of 5 to 40 mol% in total, the transition element having the maximum positive valence which is +1 or more greater than the valence of the A site ion of the ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$.

7. (Original) A ferroelectric film including a perovskite ferroelectric or a bismuth layer-structured ferroelectric shown by ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ (wherein A represents at

least one ion selected from the group consisting of Li^+, Na^+, K^+, Pb^{2+}, Ca^{2+}, Sr^{2+}, Ba^{2+}, Bi^{3+} and La^{3+}, B represents at least one ion selected from the group consisting of Fe^{3+}, Ti^{4+}, Zr^{4+}, Nb^{5+}, Ta^{5+}, W^{6+} and Mo^{6+}, and m is a natural number),

wherein at least four-fold coordinated Si^{4+} or Ge^{4+} is included in the A site ion;

wherein the ferroelectric film is a solid solution with a dielectric shown by X_2SiO_5, $X_4Si_3O_{12}$, X_2GeO_5 or $X_4Ge_3O_{12}$ (wherein X represents Bi^{3+}, Fe^{3+}, Sc^{3+}, Y^{3+}, La^{3+}, Ce^{3+}, Pr^{3+}, Nd^{3+}, Pm^{3+}, Sm^{3+}, Eu^{3+}, Gd^{3+}, Tb^{3+}, Dy^{3+}, Ho^{3+}, Er^{3+}, Tm^{3+}, Yb^{3+} or Lu^{3+}); and

wherein the ferroelectric film includes at least one transition element in an amount of 5 to 40 mol% in total, the transition element having the maximum positive valence which is +1 or more greater than the valence of the B site ion of the ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$

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8. (Original) A ferroelectric film including a perovskite ferroelectric or a bismuth layer-structured ferroelectric shown by ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ (wherein A represents at least one ion selected from the group consisting of Li^+, Na^+, K^+, Pb^{2+}, Ca^{2+}, Sr^{2+}, Ba^{2+}, Bi^{3+} and La^{3+}, B represents at least one ion selected from the group consisting of Fe^{3+}, Ti^{4+}, Zr^{4+}, Nb^{5+}, Ta^{5+}, W^{6+} and Mo^{6+}, and m is a natural number),

wherein at least four-fold coordinated Si^{4+} or Ge^{4+} is included in the A site ion;

wherein the ferroelectric film is a solid solution with a dielectric shown by X_2SiO_5, $X_4Si_3O_{12}$, X_2GeO_5 or $X_4Ge_3O_{12}$ (wherein X represents Bi^{3+}, Fe^{3+}, Sc^{3+}, Y^{3+}, La^{3+}, Ce^{3+}, Pr^{3+}, Nd^{3+}, Pm^{3+}, Sm^{3+}, Eu^{3+}, Gd^{3+}, Tb^{3+}, Dy^{3+}, Ho^{3+}, Er^{3+}, Tm^{3+}, Yb^{3+} or Lu^{3+});

wherein the ferroelectric film includes at least one transition element having the maximum positive valence which is +1 or more greater than the valence of the B site ion of the ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$;

wherein the ferroelectric film includes at least one transition element having the maximum positive valence which is +1 or more greater than the valence of the A site ion of the ABO_3 or $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$; and

wherein the transition elements are included in an amount of 5 to 40 mol% in the A and B sites in total.

9. (Currently Amended) The ferroelectric film as defined in ~~any of claims 1 to 8,~~ claim 1, wherein the ferroelectric film includes Pb(Zr, Ti)O_3 which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the A site ion in an amount of 1% or more; and

wherein at least one transition element having the maximum positive valence of +3 or more is included in the A site in an amount of 5 to 40 mol% in total.

10. (Currently Amended) The ferroelectric film as defined in ~~any of claims 1 to 8,~~ claim 1, wherein the ferroelectric film includes Pb(Zr, Ti)O_3 which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the A site ion in an amount of 1% or more; and

wherein at least one transition element having the maximum positive valence of +5 or more is included in the B site in an amount of 5 to 40 mol% in total.

11. (Original) A ferroelectric film including Pb(Zr, Ti)O_3 which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Pb site ion in an amount of 1% or more,

wherein at least one transition element having the maximum positive valence of +3 or more is included in the Pb site;

wherein at least one transition element having the maximum positive valence of +5 or more is included in the Zr or Ti site; and

wherein the transition elements are included in an mount of 5 to 40 mol% in the Pb and Zr or Ti sites in total.

12. (Original) A ferroelectric film including $Pb(Zr, Ti)O_3$ which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Pb site ion in an amount of 1% or more,

wherein at least one of La and other lanthanoid series ions is included in the Pb site in an amount of 5 to 40 mol% in total.

13. (Original) A ferroelectric film including $Pb(Zr, Ti)O_3$ which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Pb site ion in an amount of 1% or more,

wherein at least one of Nb, V and W is included in the Zr or Ti site in an amount of 5 to 40 mol% in total.

14. (Original) A ferroelectric film including $Pb(Zr, Ti)O_3$ which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Pb site ion in an amount of 1% or more,

wherein at least one of La and other lanthanoid series ions is included in the Pb site, and at least one of Nb, V and W is included in the Zr or Ti site, in an amount of 5 to 40 mol% in the Pb and Zr or Ti sites in total.

15. (Currently Amended) The ferroelectric film as defined in ~~any of claim 11 to 14,~~ claim 11, further including:

at least one of Nb, V and W in the Zr or Ti site in an amount twice the amount of Pb ion vacancy in the Pb site.

16. (Currently Amended) The ferroelectric film as defined in ~~any of claims 11 to 14~~ claim 11 is included (111)-oriented tetragonal crystals.

17. (Currently Amended) The ferroelectric film as defined in ~~any of claims 11 to 14~~ claim 11 is included (001)-oriented rhombohedral crystals.

18. (Original) A method of manufacturing a ferroelectric film including $Pb(Zr,Ti)O_3$, the method comprising:

using a sol-gel solution for forming $Pb(Zr,Ti)O_3$ which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Pb site ion in an amount of 1% or more.

19. (Original) A method of manufacturing a ferroelectric film including $Pb(Zr,Ti)O_3$, the method comprising:

using a sol-gel solution for forming $Pb(Zr,Ti)O_3$ which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Pb site ion in an amount of 1% or more,

wherein a mixed solution prepared by mixing a sol-gel solution for forming $PbZrO_3$ which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Pb site ion in an amount of 1% or more with a sol-gel solution for forming $PbTiO_3$ which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Pb site ion in an amount of 1% or more is used as the sol-gel solution for forming $Pb(Zr,Ti)O_3$.

20. (Original) A method of manufacturing a ferroelectric film including $Pb(Zr,Ti)O_3$, the method comprising:

using a sol-gel solution for forming $Pb(Zr,Ti)O_3$ in which the amount of Pb ranges from 90 to 120% of the stoichiometric composition of $Pb(Zr,Ti)O_3$.

21. (Currently Amended) The ferroelectric film as defined in ~~any of claims 1 to 8,~~ claim 1, wherein the ferroelectric film includes $Bi_4Ti_3O_{12}$ including at least four-fold coordinated Si^{4+} or Ge^{4+} in the A site ion in an amount of 1% or more; and

wherein at least one transition element having the maximum positive valence of +4 or more is included in the A site in an amount of 5 to 40 mol% in total.

22. (Currently Amended) The ferroelectric film as defined in ~~any of claims 1 to 8,~~ claim 1, wherein the ferroelectric film includes $Bi_4Ti_3O_{12}$ including at least four-fold coordinated Si^{4+} or Ge^{4+} in the A site ion in an amount of 1% or more; and

wherein at least one transition element having the maximum positive valence of +5 or more is included in the B site in an amount of 5 to 40 mol% in total.

23. (Original) A ferroelectric film including $Bi_4Ti_3O_{12}$ including at least four-fold coordinated Si^{4+} or Ge^{4+} in the Bi site ion in an amount of 1% or more,

wherein at least one transition element having the maximum positive valence of +4 or more is included in the Bi site;

wherein at least one transition element having the maximum positive valence of +5 or more is included in the Ti site; and

wherein the transition elements are included in an amount of 5 to 40 mol% in the Bi and Ti sites in total.

24. (Original) A ferroelectric film including $Bi_4Ti_3O_{12}$ including at least four-fold coordinated Si^{4+} or Ge^{4+} in the Bi site ion in an amount of 1% or more,

wherein at least one of Nb, V and W is included in the Ti site in an amount of 5 to 40 mol% in total.

25. (Currently Amended) The ferroelectric film as defined in ~~claim 23 or 24,~~ claim 23, further including:

at least one of Nb, V, and W in the Ti site in an amount twice the amount of Bi ion vacancy in the Bi site.

26. (Currently Amended) The ferroelectric film as defined in ~~claim 23 or 24~~ claim 23 is included (111), (110), and (117) oriented orthorhombic crystals.

27. (Original) A method of manufacturing a ferroelectric film including $Bi_4Ti_3O_{12}$, the method comprising:

using a sol-gel solution for forming $Bi_4Ti_3O_{12}$ which includes at least four-fold coordinated Si^{4+} or Ge^{4+} in the Bi site ion in an amount of 1% or more.

28. (Original) A method of manufacturing a ferroelectric film including $Bi_4Ti_3O_{12}$, the method comprising:

using a mixed solution prepared by mixing a solution prepared by mixing a sol-gel solution for forming Bi_2O_3 with a sol-gel solution for forming TiO_2 at a molar ratio of 2:3 with a sol-gel solution for forming a dielectric shown by X_2SiO_5, $X_4Si_3O_{12}$, X_2GeO_5, or $X_4Ge_3O_{12}$ (wherein X represents Bi^{3+}, Fe^{3+}, Sc^{3+}, Y^{3+}, La^{3+}, Ce^{3+}, Pr^{3+}, Nd^{3+}, Pm^{3+}, Sm^{3+},

Eu^{3+}, Gd^{3+}, Tb^{3+}, Dy^{3+}, Ho^{3+}, Er^{3+}, Tm^{3+}, Yb^{3+}, or Lu^{3+}) so that Si^{4+} or Ge^{4+} is included in an amount of 1 mol% or more.

29. (Original) A method of manufacturing a ferroelectric film including $Bi_4Ti_3O_{12}$, the method comprising:

using a sol-gel solution for forming $Bi_4Ti_3O_{12}$ in which an excess amount of Bi ranges from 90 to 120% of the stoichiometric composition of $Bi_4Ti_3O_{12}$.

30. (Currently Amended) A ferroelectric memory comprising the ferroelectric film as defined in ~~any of claims 1 to 17 and 21 to 26.~~ claim 1.

31. (Currently Amended) A piezoelectric device comprising the ferroelectric film as defined in ~~any of claims 1 to 7 and 21 to 26.~~ claim 1.